

## Driver Transistors

PNP Silicon

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

#### **Features**

- € S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AïEc101 Qualified and PPAP Capable
- € These Devices are Rbree, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

|           |   | Rating | Symbol | Value | Unit |  |
|-----------|---|--------|--------|-------|------|--|
| Collector | ï |        | I I    | ı     | I    |  |

### MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ °C unless otherwise noted)

| Characteristic   | Symbol                | Min        | Max    | Unit |
|--|-----------------------|------------|--------|------|
| OFF CHARACTERISTICS  |                       |            |        |      |
| Collector ïEmitter Breakdown Voltage (Note 3) (I <sub>C</sub> = ï1.0 mAdc, I <sub>B</sub> = 0) MMBTA55 MMBTA56, SMMBTA56   | V <sub>(BR)</sub> CEO | ï60<br>ï80 | ï<br>ï | Vdc  |
| Emitter ïBase Breakdown Voltage (I <sub>E</sub> = ï100 Adc, I <sub>C</sub> = 0)  | V <sub>(BR)EBO</sub>  | ï4.0       | ï      | Vdc  |
| Collector Cutoff Current (V <sub>CE</sub> = ï60 Vdc, I <sub>B</sub> = 0)   | I <sub>CES</sub>      | ï          | ï0.1   | Adc  |
| Collector Cutoff Current   | Ісво                  | ï          | ï0.1   | Adc  |
| ON CHARACTERISTICS   |                       |            |        |      |
| DC Current Gain ( $I_C = \ddot{1}10 \text{ mAdc}$ , $V_{CE} = \ddot{1}1.0 \text{ Vdc}$ ) ( $I_C = \ddot{1}100 \text{ mAdc}$ , $V_{CE} = \ddot{1}1.0 \text{ Vdc}$ ) | h <sub>FE</sub>       | 100<br>100 | ï<br>ï | ï    |
| Collector ïEmitter Saturation Voltage (I <sub>C</sub> = ï100 mAdc, I <sub>B</sub> = ï10 mAdc)  | V <sub>CE(sat)</sub>  | ï          | ï0.25  | Vdc  |
| Base ï Emitter On Voltage<br>(I <sub>C</sub> = ï100 mAdc, V <sub>CE</sub> = ï1.0 Vdc)  | V <sub>BE(on)</sub>   | ï          | ï1.2   | Vdc  |
| SMALL TSIGNAL CHARACTERISTICS  | <u> </u>              |            | •      | •    |
| Current ïGain ï Bandwidth Product (Note 4)<br>(I <sub>C</sub> = ï100 mAdc, V <sub>CE</sub> = ï1.0 Vdc, f = 100 MHz)  | f <sub>T</sub>        | 50         | ï      | MHz  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 s, Duty Cycle ≤ 2.0%.

4. f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

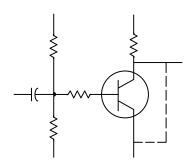
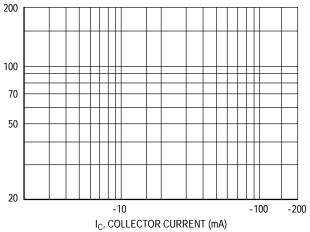
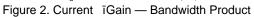


Figure 1. Switching Time Test Circuits

## MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series





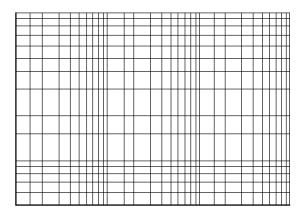


Figure 3. Capacitance

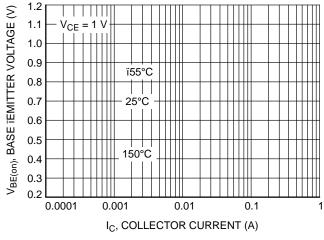


Figure 8. Base Emitter Voltage vs. Collector Current

Figure 9. Collector Saturation Region

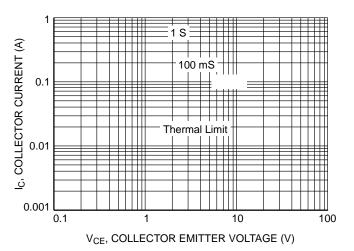


Figure 10. Base ïEmitter Temperature Coefficient

Figure 11. Safe Operating Area

# ${\sf MMBTA55L~Series},\,{\sf MMBTA56L~Series},\,{\sf SMMBTA56L~Series}$

#### PACKAGE DIMENSIONS

SOT ï23 (TO ï236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

RECOMMENDF